



#6/Amend  
1/2/00  
7-19-00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Kiyoshi IRINO

Serial No.: 09/428,052

Group Art Unit: 2815

Filed: October 27, 1999

Examiner: J. Diaz

For: METHOD OF FABRICATING A SEMICONDUCTOR DEVICE CONTAINING  
NITROGEN IN A GATE OXIDE FILM (AS AMENDED)

AMENDMENT

Director of Patents and Trademarks  
Washington, D.C. 20231

July 7, 2000

Sir:

In response to the Office Action dated March 9, 2000, please amend the above-identified  
application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 11, line 11, change ~~“ , and”~~ to --. As shown in Fig. 5G,--.

Page 14, line 34, change ~~“ , and”~~ to --. As shown in Fig. 7G,--.

IN THE CLAIMS:

Please amend claims 9 and 10 as follows:

Claim 9, line 1, change ~~“9”~~ to --7--.

Claim 10, line 1, change ~~“7”~~ to --6--.

line 2, change ~~“asid”~~ to --said--.

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